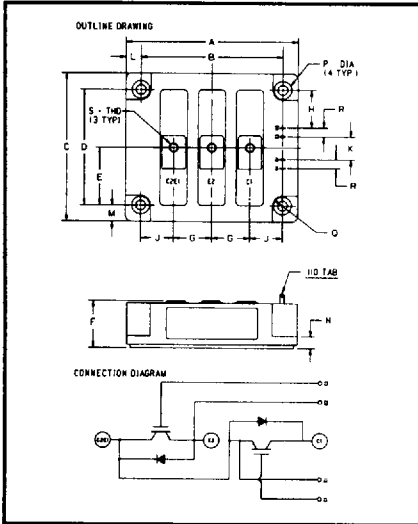
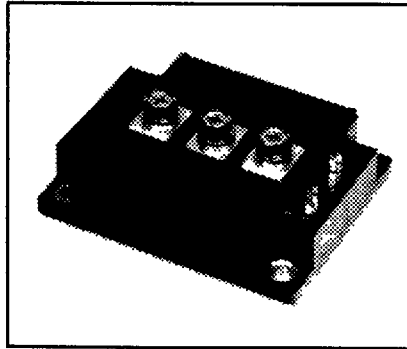


Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

Dual IGBTMOD™ E-Series Module 300 Amperes/1200 Volts



CM300DY-24.E
Outline Drawing



CM300DY-24E
Dual IGBTMOD™ E-Series Module
300 Amperes/1200 Volts

Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery (150ns) Free-Wheel Diode
- ☐ High Frequency Operation (15-20kHz)
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below
-i.e. CM300DY-24E is a 1200V (V_{CES}), 300 Ampere Dual IGBTMOD™ Power Module.

Dimensions	Inches	Millimeters
A	4.45	113.0
B	3.661±0.01	93.0±0.25
C	3.74	95.0
D	2.992±0.01	76.0±0.25
E	1.50	38.0
F	1.22 Max.	31.0 Max.
G	0.98	25.0
H	0.96	24.5
J	0.85	21.5
K	0.59	15.0
L	0.39	10.0
M	0.37	9.5
N	0.28	7.0
P	0.26 Dia.	Dia. 6.5
Q	0.26 R	R 6.5
R	0.24	6.0
S	M6 Metric	M6

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	300	24

Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

CM300DY-24E

Dual IGBTMOD™ E-Series Module

300 Amperes/1200 Volts

Absolute Maximum Ratings, $T_J = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM300DY-24E	Units
Junction Temperature	T_J	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage	V_{GES}	± 20	Volts
Collector Current	I_C	300	Amperes
Peak Collector Current	I_{CM}	600*	Amperes
Diode Forward Current	I_{FM}	300	Amperes
Diode Forward Surge Current	I_{FM}	600*	Amperes
Power Dissipation	P_d	2100	Watts
Max. Mounting Torque M6 Terminal Screws	—	26	in-lb
Max. Mounting Torque M6 Mounting Screws	—	26	in-lb
Module Weight (Typical)	—	740	Grams
V Isolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating

Static Electrical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0\text{V}$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0\text{V}$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 30\text{mA}, V_{CE} = 10\text{V}$	3.5	5.0	6.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 300\text{A}, V_{GE} = 15\text{V}$	—	—	4.0**	Volts
		$I_C = 300\text{A}, V_{GE} = 15\text{V}, T_J = 150^\circ\text{C}$	—	—	4.0**	Volts
Total Gate Charge	Q_G	$V_{CC} = 600\text{V}, I_C = 300\text{A}, V_{GS} = 15\text{V}$	—	3200	—	nC
Diode Forward Voltage	V_{FM}	$I_E = 300\text{A}, V_{GS} = 0\text{V}$	—	—	2.5	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible

Dynamic Electrical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{GE} = 0\text{V}, V_{CE} = 10\text{V}, f = 1\text{MHz}$	—	—	120	nF
Output Capacitance	C_{oes}		—	—	36	nF
Reverse Transfer Capacitance	C_{res}		—	—	24	nF
Resistive	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 300\text{A}, V_{GE1} = V_{GE2} = 15\text{V}, R_G = 1.0\Omega$	—	—	400	ns
	Rise Time		—	—	600	ns
Switch Times	Turn-off Delay Time		—	—	600	ns
	Fall Time		—	—	400	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 300\text{A}, di_E/dt = -600\text{A}/\mu\text{s}$	—	—	300	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 300, di_E/dt = -600\text{A}/\mu\text{s}$	—	6.6	—	μC

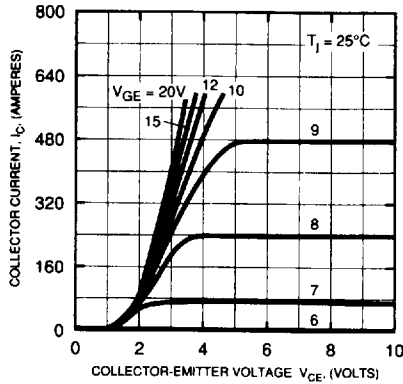
Thermal and Mechanical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	—	—	0.06	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per Free Wheel Diode	—	—	0.12	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Half Module	—	—	0.06	$^\circ\text{C}/\text{W}$

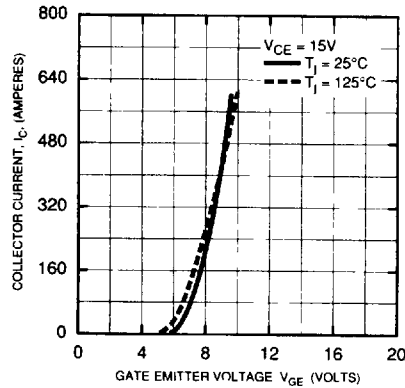
Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

CM300DY-24E
Dual IGBTMOD™ E-Series Module
300 Amperes/1200 Volts

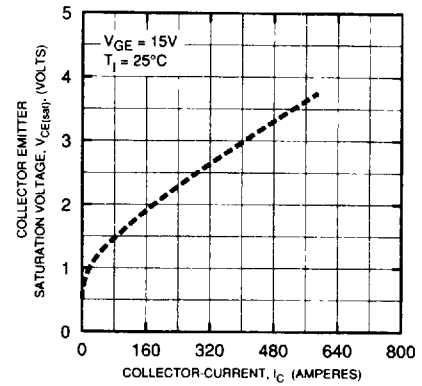
OUTPUT CHARACTERISTICS
(TYPICAL)



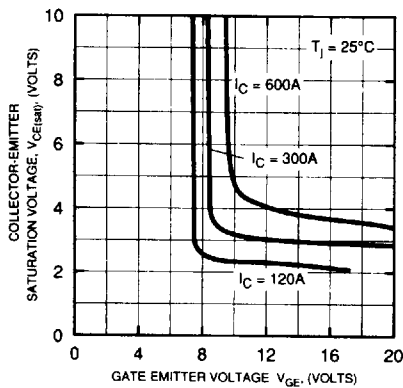
TRANSFER CHARACTERISTICS
(TYPICAL)



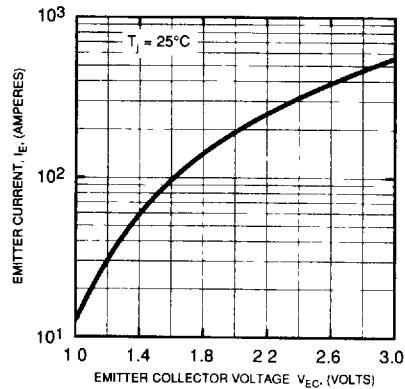
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



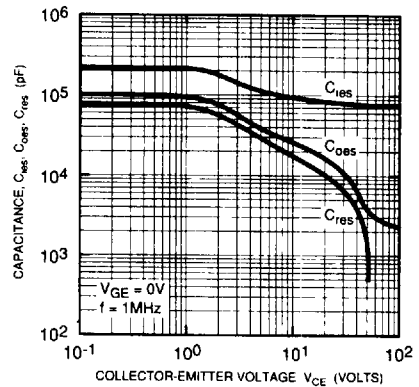
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



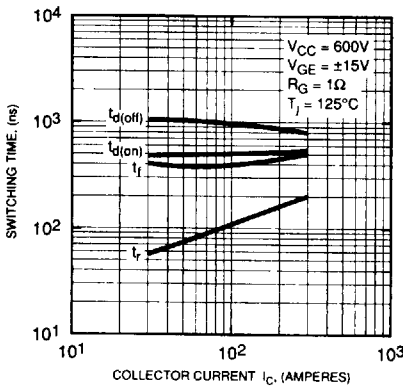
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



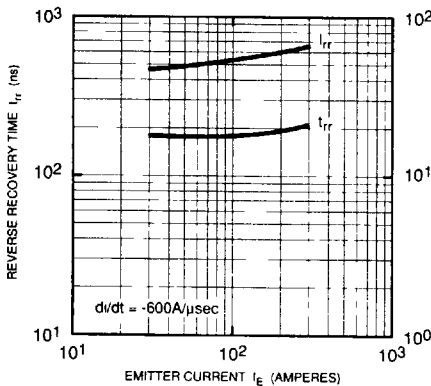
CAPACITANCE VS. V_{CE}
(TYPICAL)



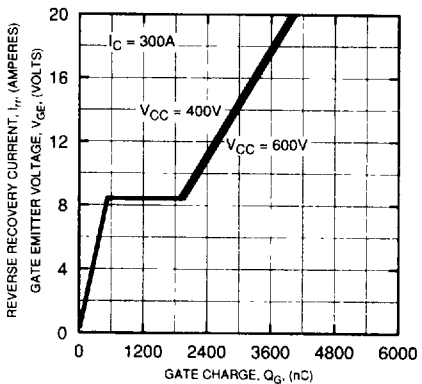
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)

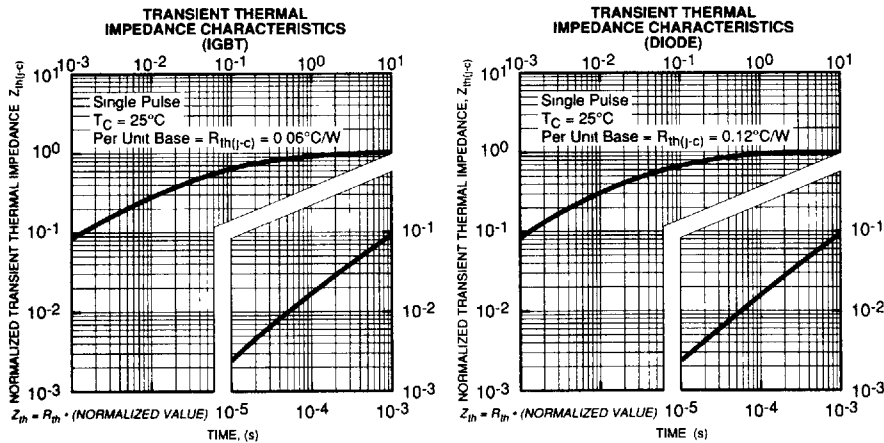


GATE CHARGE, V_{GE}

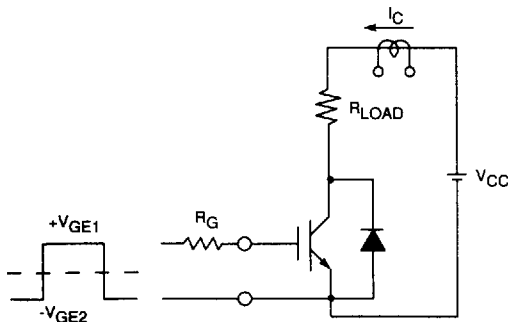


Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

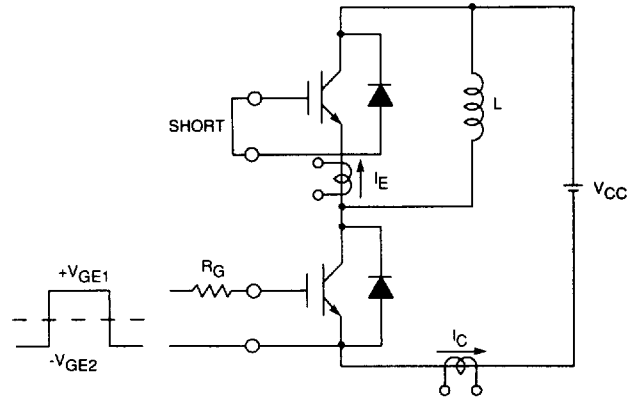
CM300DY-24E
Dual IGBTMOD™ E-Series Module
300 Amperes/1200 Volts



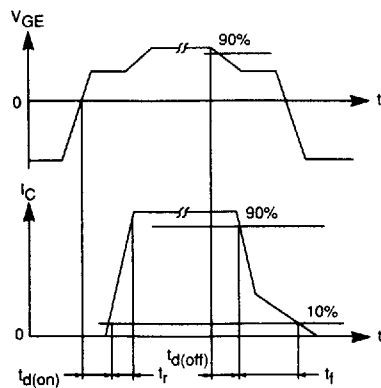
SWITCHING TIME TEST CIRCUITS & WAVEFORMS



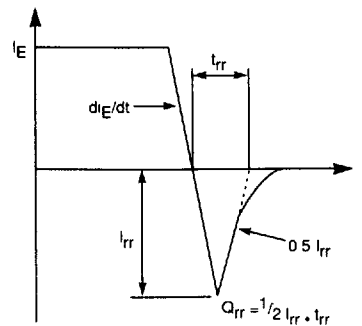
RESISTANCE LOAD SWITCHING TEST CIRCUIT



HALF-BRIDGE SWITCHING TEST CIRCUIT



SWITCHING TIME TEST WAVEFORMS



t_{rr} , Q_{rr} WAVEFORMS